

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device according to the present invention comprises a laminated structure of a semiconductor material including an active layer formed of a quantum well structure, a low-reflection film formed on one end face of the structure, and a high-reflection film formed on the other end face of the structure. The cavity length (L) of the device is 1,200 μm or more. This laser device, which enjoys high kink currents and a satisfactorily linear current-optical output characteristic, is a useful pumping light source for optical fiber amplifier.